

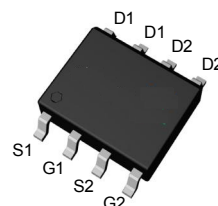
Features

- 30V/8A,
 $R_{DS(ON)} = 23m\Omega(max.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 27m\Omega(max.) @ V_{GS} = 4.5V$
 $R_{DS(ON)} = 45m\Omega(max.) @ V_{GS} = 2.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- 100% UIS Tested

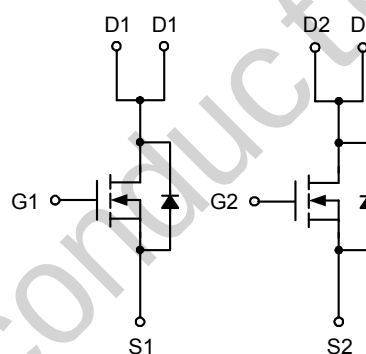
Applications

- Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems.

Pin Description



Top View of SOP-8



N-Channel MOSFET

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±12	
I _D ^a	Continuous Drain Current (V _{GS} =10V)	T _A =25°C 8 T _A =70°C 6.5	A
I _{DM} ^a	300μs Pulsed Drain Current (V _{GS} =10V)	40	
I _S ^a	Diode Continuous Forward Current	1	
I _{AS} ^b	Avalanche Current (Single Pulse)	9	
E _{AS} ^b	Avalanche Energy, Single Pulse (L=0.5mH)	20	mJ
T _J	Maximum Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to 150	
P _D ^a	Maximum Power Dissipation	T _A =25°C 1.7 T _A =70°C 1.08	W
R _{θJA} ^a	Thermal Resistance-Junction to Ambient	t ≤ 10s 48 Steady State 74	
R _{θJL}	Thermal Resistance-Junction to Lead	Steady State 32	°C/W

Note a : Surface Mounted on 1in² pad area, t ≤ 10sec. Maximum Power dissipation is calculated from R_{θJA} (worst) = 62.5 °C/W under t ≤ 10s.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_J=25°C).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	4800			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	0.6	0.9	1.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =8A	-	23	28	mΩ
		V _{GS} =4.5V, I _{DS} =7A	-	27	37	
		V _{GS} =2.5V, I _{DS} =7A	-	35	45	
Gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =8A	-	32	-	S
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =1A, V _{GS} =0V	-	0.7	1.1	V
t _{rr} ^b	Reverse Recovery Time	I _{SD} =8A, dl _{SD} /dt=100A/μs	-	15.5	-	ns
Q _{rr} ^b	Reverse Recovery Charge		-	6.5	-	nC

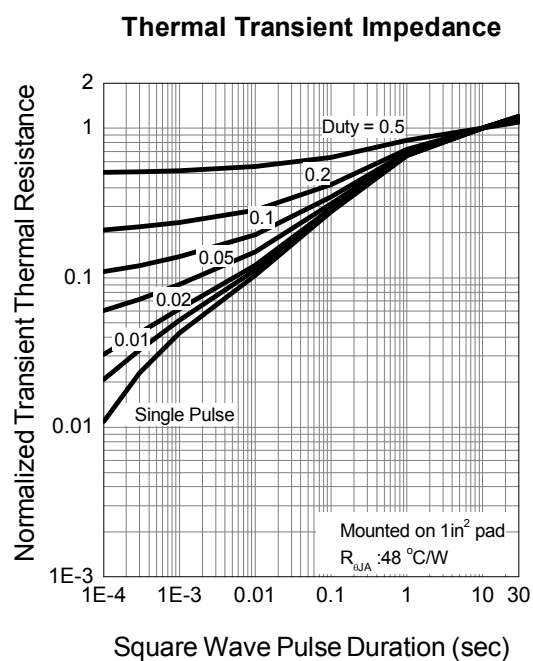
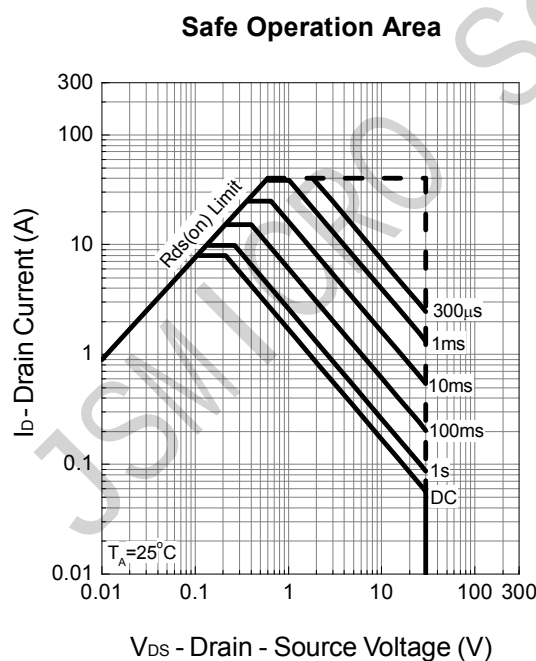
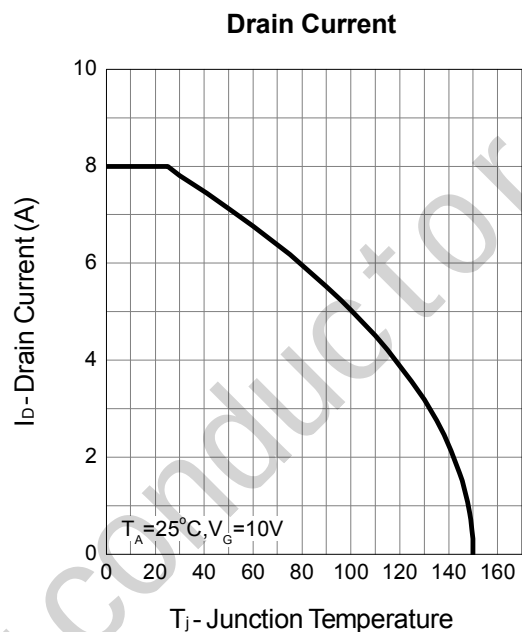
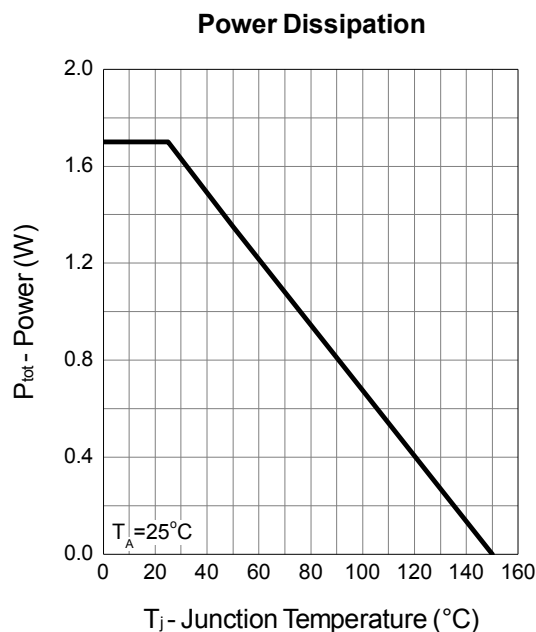
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	4800			Unit
			Min.	Typ.	Max.	
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	1.3	1.7	2.3	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, Frequency=1.0MHz	-	580	-	pF
C _{oss}	Output Capacitance		-	95	-	
C _{rss}	Reverse Transfer Capacitance		-	57	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =15V, R _L =15Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	5.9	10	ns
t _r	Turn-on Rise Time		-	10	17	
t _{d(OFF)}	Turn-off Delay Time		-	17	35	
t _f	Turn-off Fall Time		-	4	9	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =8A	-	10.2	14	nC
	Total Gate Charge		-	5.3	-	
Q _{gth}	Threshold Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _{DS} =8A	-	0.78	-	
Q _{gs}	Gate-Source Charge		-	1.7	-	
Q _{gd}	Gate-Drain Charge		-	2.2	-	

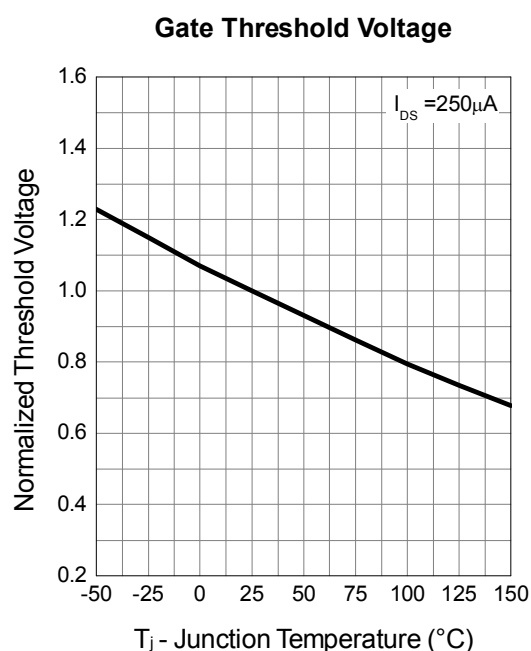
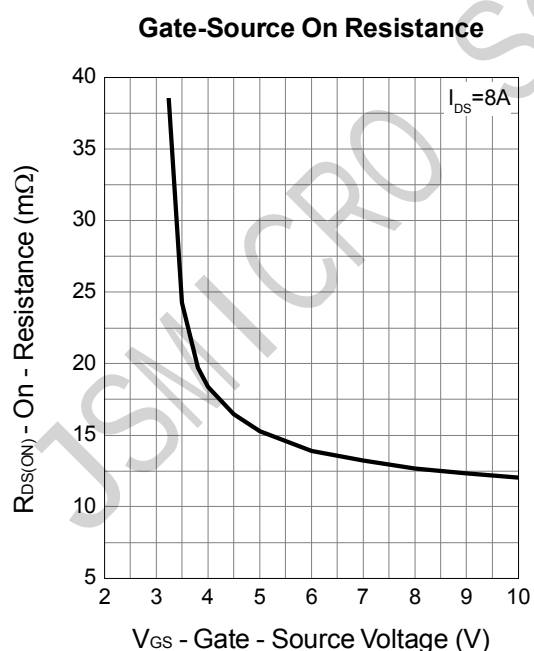
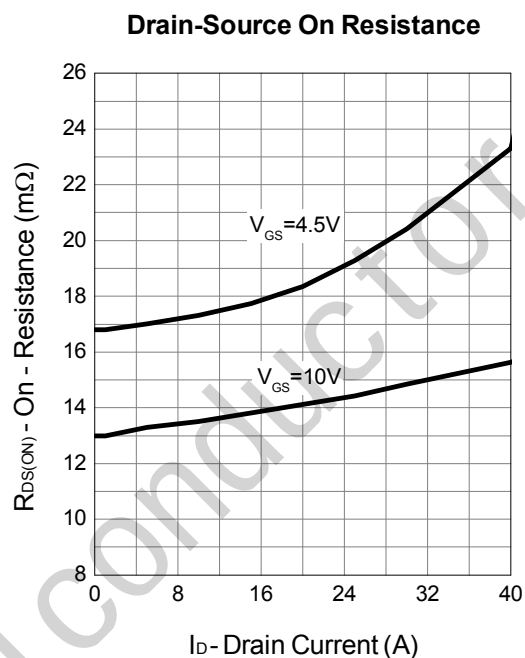
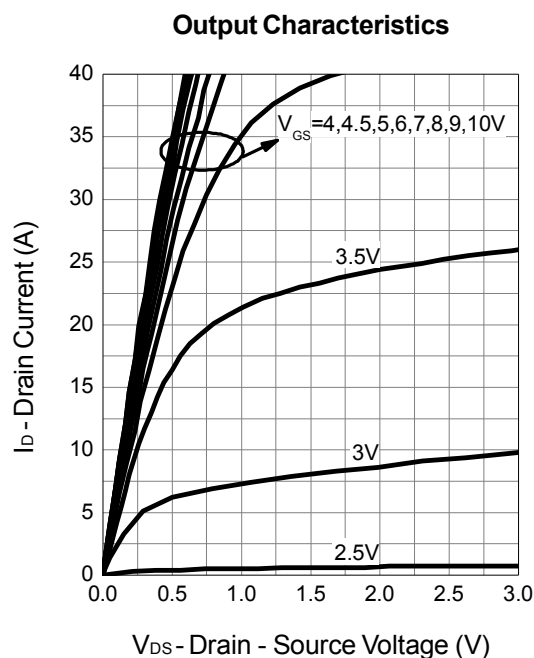
Note a : Pulse test ; pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$.

Note b : Guaranteed by design, not subject to production testing.

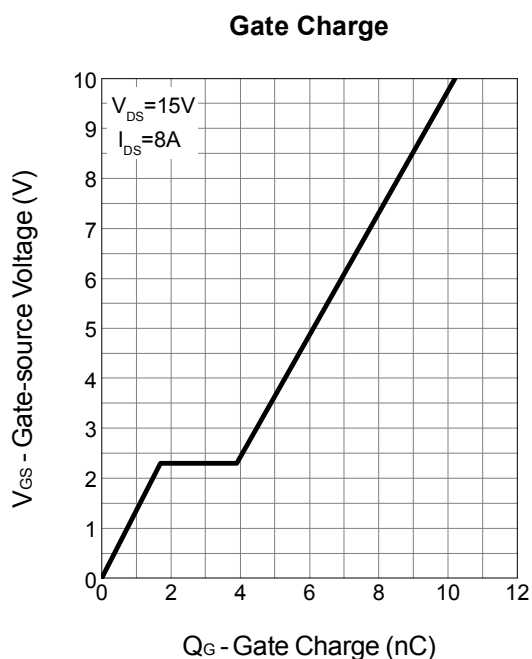
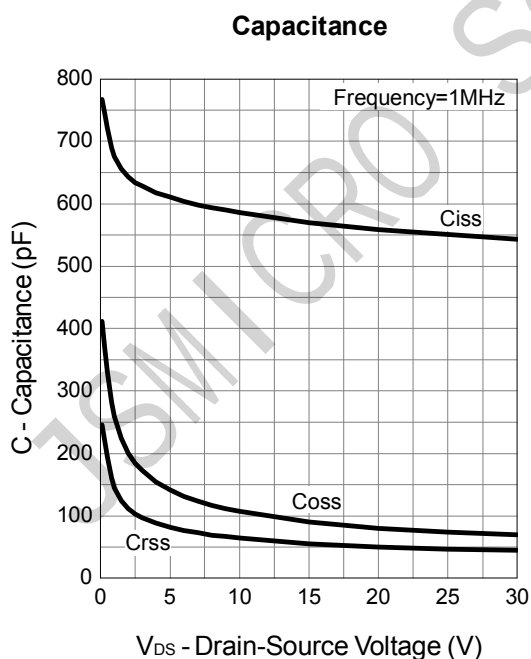
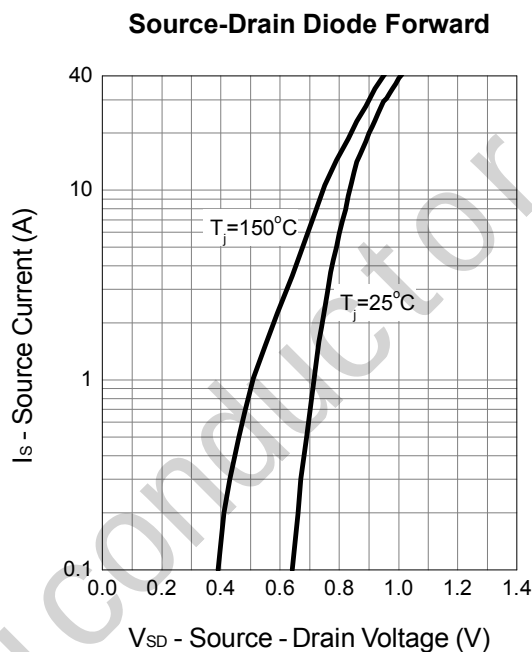
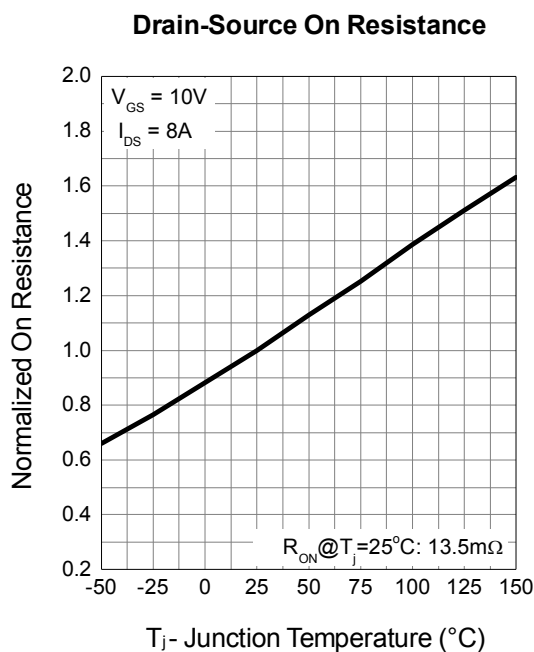
Typical Operating Characteristics



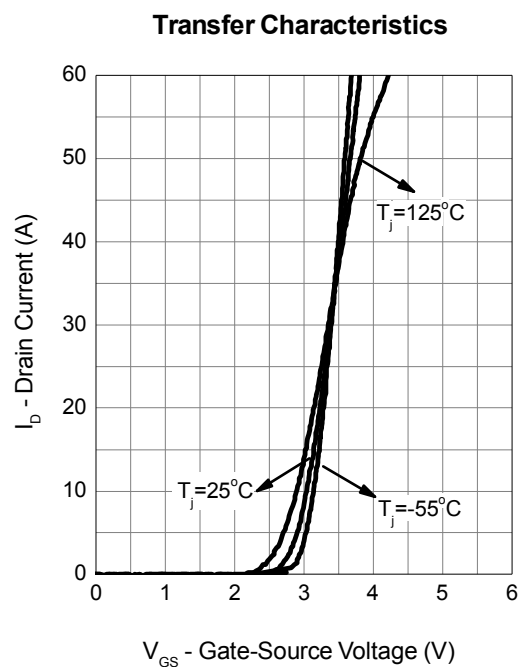
Typical Operating Characteristics (Cont.)



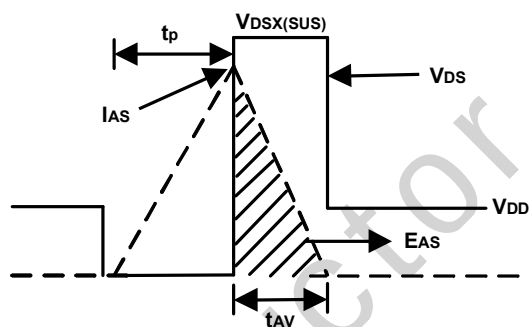
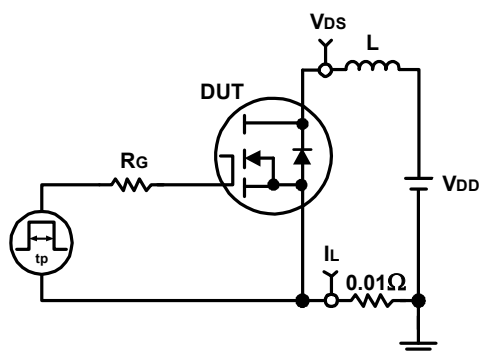
Typical Operating Characteristics (Cont.)



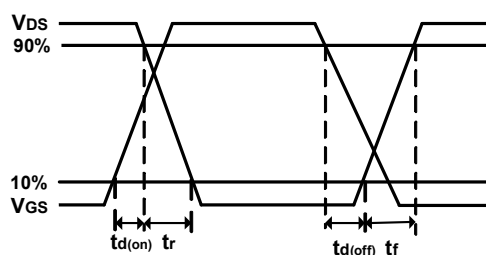
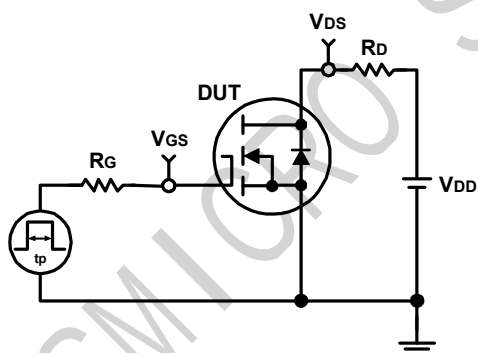
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

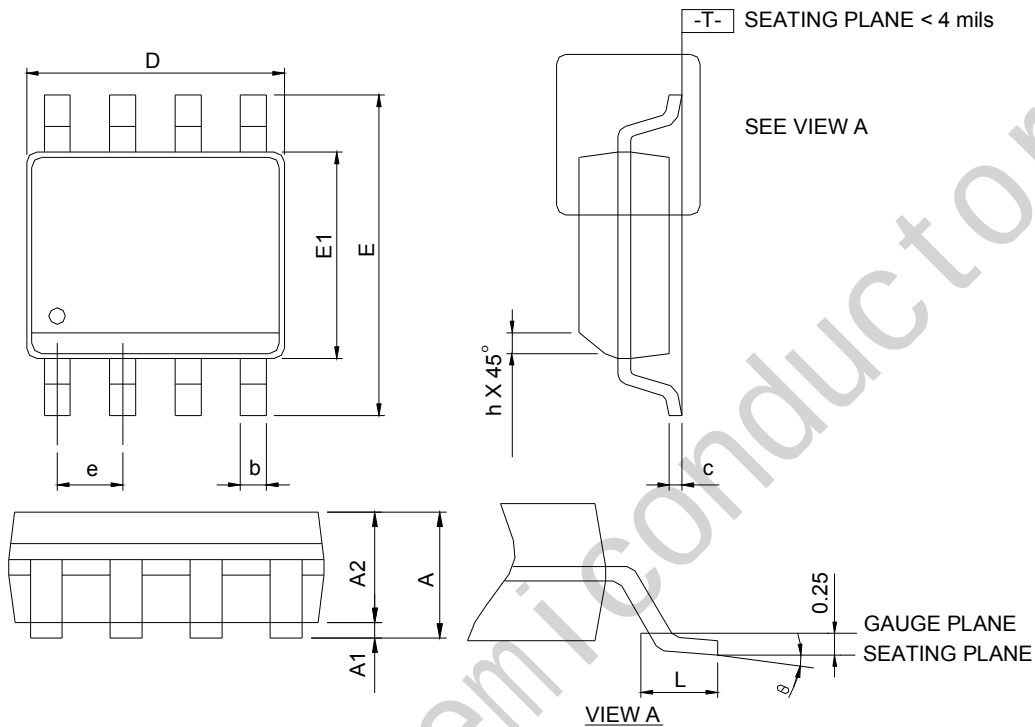


Switching Time Test Circuit and Waveforms



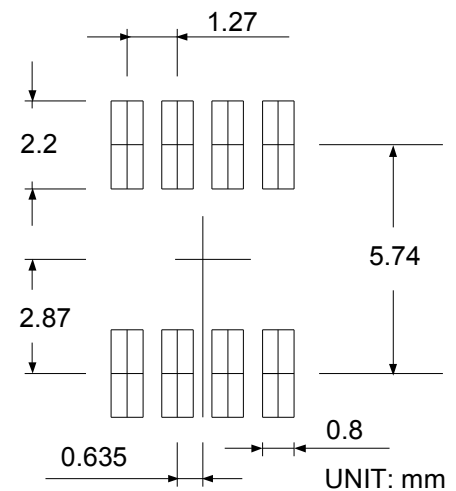
Package Information

SOP-8



	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



- Note: 1. Follow JEDEC MS-012 AA.
2. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
3. Dimension "E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.